Octal 3-State Noninverting D Flip-Flop with LSTTL-Compatible Inputs High-Performance Silicon-Gate CMOS

The MC74HCT574A is identical in pinout to the LS574. This device may be used as a level converter for interfacing TTL or NMOS outputs to High Speed CMOS inputs.

Data meeting the setup time is clocked to the outputs with the rising edge of the Clock. The Output Enable input does not affect the states of the flip-flops, but when Output Enable is high, all device outputs are forced to the high-impedance state. Thus, data may be stored even when the outputs are not enabled.

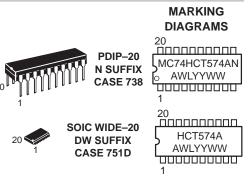
The HCT574A is identical in function to the HCT374A but has the flip—flop inputs on the opposite side of the package from the outputs to facilitate PC board layout.

- Output Drive Capability: 15 LSTTL Loads
- TTL NMOS Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μA
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 286 FETs or 71.5 Equivalent Gates



ON Semiconductor

http://onsemi.com



A = Assembly Location

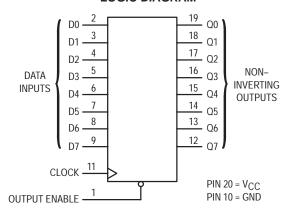
WL = Wafer Lot YY = Year

WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC74HCT574AN	PDIP-20	1440 / Box
MC74HCT574ADW	SOIC-WIDE	38 / Rail
MC74HCT574ADWR2	SOIC-WIDE	1000 / Reel

LOGIC DIAGRAM



FUNCTION TABLE

Inputs			Output
OE	Clock	D	Q
L		Н	Н
L		L	L
L	L,H,⁻∕_	Х	No Change
Н	Х	Х	Z

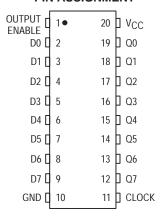
X = don't care

Z = high impedance

Design Criteria	Value	Units
Internal Gate Count*	71.5	ea
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	0.0075	рЈ

^{*}Equivalent to a two-input NAND gate.

PIN ASSIGNMENT



MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
VCC	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
lin	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 35	mA
ICC	DC Supply Current, V _{CC} and GND Pins	± 75	mA
PD	Power Dissipation in Still Air, Plastic DIP† SOIC Package†	750 500	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq VCC. Unused inputs must always be tied to an appropriate logic voltage

level (e.g., either GND or V_{CC}). Unused outputs must be left open.

SOIC Package: -7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
Vcc	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	Vcc	V
T _A	Operating Temperature, All Package Types	- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	0	500	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
VIH	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V _{IL}	Maximum Low–Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
VOH	Minimum High-Level Output Voltage	$V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}}$ $ I_{\text{Out}} \le 20 \ \mu\text{A}$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{Out} \le 6.0 \text{ mA}$	4.5	3.98	3.84	3.7	V
VOL	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu A$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{Out} \le 6.0 \text{ mA}$	4.5	0.26	0.33	0.4	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	5.5	± 0.1	± 1.0	± 1.0	μА
ICC	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 μA	5.5	4.0	40	160	μА

^{1.} Output in high-impedance state.

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

^{*}Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

[†]Derating — Plastic DIP: -10 mW/°C from 65° to 125°C

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	arante	ed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 8	5°C	≤ 125°C	Unit
loz	Maximum Three–State Leakage Current	V _{in} = V _{IL} or V _{IH} (Note 1) V _{out} = V _{CC} or GND	5.5	- 0.5	– 5	5.0	- 10	μΑ
ΔlCC	Additional Quiescent Supply Current	V _{in} = 2.4 V, Any One Input V _{in} = V _{CC} or GND, Other Inputs		≥ – 55°	С	25°0	C to 125°C	
	Current	$I_{\text{out}} = 0 \mu\text{A}$	5.5	2.9			2.4	mA

^{1.} Output in high-impedance state.

AC ELECTRICAL CHARACTERISTICS (V $_{CC}$ = 5.0 V \pm 10%, C_{L} = 50 pF, Input t_{f} = tf = 6.0 ns)

		Guaranteed Limit		nit	
Symbol	Parameter	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
f _{MAX}	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 4)	30	24	20	MHz
tPLH, tPHL	Maximum Propagation Delay, Clock to Q (Figures 1 and 4)	30	38	45	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to Q (Figures 2 and 5)	28	35	42	ns
tPZH, tPZL	Maximum Propagation Delay Time, Output Enable to Q (Figures 2 and 5)	28	35	42	ns
tTLH,	Maximum Output Transition Time, Any Output (Figures 1, 2 and 4)	12	15	18	ns
C _{in}	Maximum Input Capacitance	10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

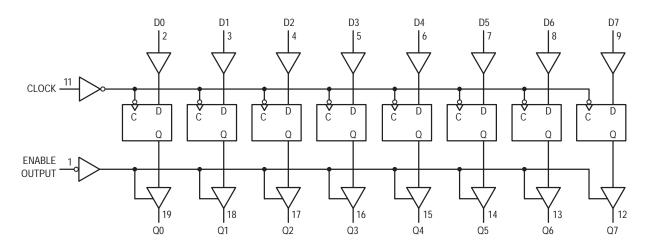
			Typical @ 25°C, V _{CC} = 5.0 V	
C	PD	Power Dissipation Capacitance (Per Flip–Flop)*	58	pF

^{*} Used to determine the no-load dynamic power consumption: PD = CPD VCC²f + ICC VCC. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS (V_{CC} = 5.0 V \pm 10%, C_L = 50 pF, Input t_f = t_f = 6.0 ns)

			Guaranteed Limit						
			– 55 to	25°C	≤ 8	5°C	≤ 12	25°C	
Symbol	Parameter	Fig.	Min	Max	Min	Max	Min	Max	Unit
t _{su}	Minimum Setup Time, Data to Clock	3	10		13		15		ns
th	Minimum Hold Time, Clock to Data	3	5.0		5.0		5.0		ns
t _W	Minimum Pulse Width, Clock	1	15		19		22		ns
t _r , If	Maximum Input Rise and Fall Times	1		500		500		500	ns

EXPANDED LOGIC DIAGRAM



SWITCHING WAVEFORMS

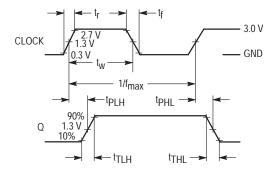


Figure 1.

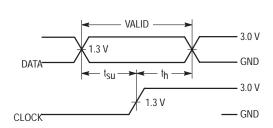


Figure 3.

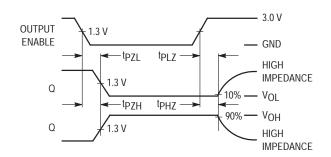
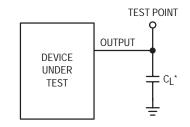
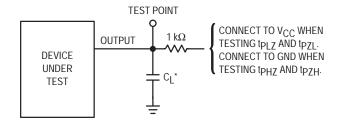


Figure 2.



*Includes all probe and jig capacitance

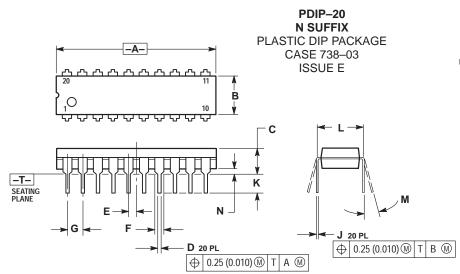
Figure 4. Test Circuit



*Includes all probe and jig capacitance

Figure 5. Test Circuit

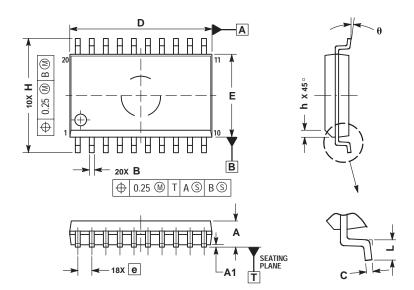
PACKAGE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
 4. DIMENSION B DOES NOT INCLUDE MOLD CI ACLI

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	1.010	1.070	25.66	27.17
В	0.240	0.260	6.10	6.60
С	0.150	0.180	3.81	4.57
D	0.015	0.022	0.39	0.55
Ε	0.050	BSC	1.27	BSC
F	0.050	0.070	1.27	1.77
G	0.100	BSC	2.54 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.140	2.80	3.55
L	0.300	BSC	7.62	BSC
M	0 °	15°	0°	15°
N	0.020	0.040	0.51	1.01

SO-20 **DW SUFFIX** CASE 751D-05 ISSUE F



- IOLES:
 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES
 PER ASME Y14.5M, 1994.

- PER ASME Y14.5M, 1994.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD
 PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 DIMENSION B DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE PROTRUSION SHALL
 BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
В	0.35	0.49		
С	0.23	0.32		
D	12.65	12.95		
Ε	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
θ	0 °	7 °		

Notes

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

NORTH AMERICA Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada

Email: ONlit@hibbertco.com

Fax Response Line: 303-675-2167 or 800-344-3810 Toll Free USA/Canada

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

EUROPE: LDC for ON Semiconductor - European Support

German Phone: (+1) 303–308–7140 (M–F 1:00pm to 5:00pm Munich Time)

Email: ONlit-german@hibbertco.com

Phone: (+1) 303-308-7141 (M-F 1:00pm to 5:00pm Toulouse Time)

Email: ONlit-french@hibbertco.com

English Phone: (+1) 303-308-7142 (M-F 12:00pm to 5:00pm UK Time)

Email: ONlit@hibbertco.com

EUROPEAN TOLL-FREE ACCESS*: 00-800-4422-3781

*Available from Germany, France, Italy, England, Ireland

CENTRAL/SOUTH AMERICA:

Spanish Phone: 303–308–7143 (Mon–Fri 8:00am to 5:00pm MST)

Email: ONlit-spanish@hibbertco.com

ASIA/PACIFIC: LDC for ON Semiconductor – Asia Support Phone: 303–675–2121 (Tue–Fri 9:00am to 1:00pm, Hong Kong Time)

Toll Free from Hong Kong & Singapore: 001-800-4422-3781

Email: ONlit-asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center 4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–8549

Phone: 81-3-5740-2745 Email: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local

Sales Representative.